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June 2014

FDA16N50_F109

N-Channel UniFETTM MOSFET

500V, 16.5 A, 380 m Ω

Features

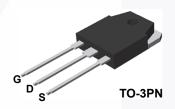
- $R_{DS(on)}$ = 380 $m\Omega$ (Max.) @ V_{GS} = 10, I_D = 8.3 A
- Low Gate Charge (Typ. 32 nC)
- Low C_{rss} (Typ. 20 pF)
- · 100% Avalanche Tested

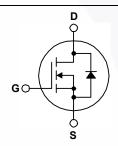
Applications

- PDP TV
- · Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDA16N50_F109	Unit			
V _{DSS}	Drain-Source Voltage			500	V			
I _D	Drain Current		- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)				A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	66	Α			
V _{GSS}	Gate-Source voltage			±30	V			
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	780	mJ			
AR	Avalanche Current		(Note 1)	16.5	Α			
E _{AR}	Repetitive Avalanche Energy		(Note 1)	20.5	mJ			
dv/dt	Peak Diode Recovery dv/dt (N		(Note 3)	4.5	V/ns			
P_{D}	Power Dissipation	(T _C = 25°C) - Derate above 25°C		205 2.1	W W/°C			
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C			
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		ose,	300	°C			

Thermal Characteristics

Symbol	Parameter	FDA16N50_F109	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/VV	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA16N50	FDA16N50_F109	TO-3PN	Tube	N/A	30 units

Electrical Characteristics $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics			ı		
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	500			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V V _{DS} = 400V, T _C = 125°C			1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	Gate-Body Leakage Current, Reverse $V_{GS} = -30V$, $V_{DS} = 0V$			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 8.3A		0.31	0.38	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 8.3A		23		S
Dynamic C	haracteristics			•	•	
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,	\	1495	1945	pF
C _{oss}	Output Capacitance	f = 1.0MHz		235	310	pF
C _{rss}	Reverse Transfer Capacitance			20	30	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250V, I _D = 16A		40	90	ns
t _r	Turn-On Rise Time	$R_G = 25\Omega$	-	150	310	ns
t _{d(off)}	Turn-Off Delay Time			65	140	ns
t _f	Turn-Off Fall Time	(Note 4)		80	170	ns
Qg	Total Gate Charge	V _{DS} = 400V, I _D = 16A	/	32	45	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V	-	8.5		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		14		nC
Drain-Sour	ce Diode Characteristics and Maximur	n Ratings		I .		
I _S	Maximum Continuous Drain-Source Diode Forward Current				9.2	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				37	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 16.5A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 16A	-	490	-	ns
Q _{rr}	Reverse Recovery Charge	dl _F /dt =100A/μs		5.0		μC

NOTES:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature

^{2.} L = 5.1mH, I_{AS} = 16.5A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C

^{3.} $I_{SD} \leq$ 16.5A, di/dt \leq 200A/ μ s, $V_{DD} \leq$ BV $_{DSS}$, Starting T $_{J}$ = 25°C

^{4.} Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

Figure 1. On-Region Characteristics

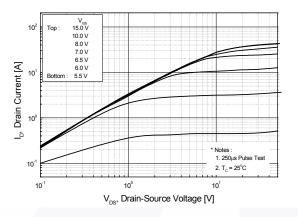


Figure 2. Transfer Characteristics

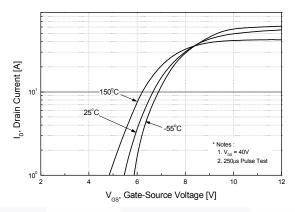
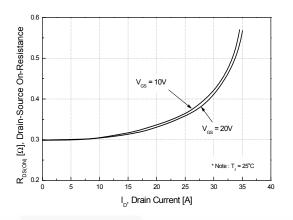


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage





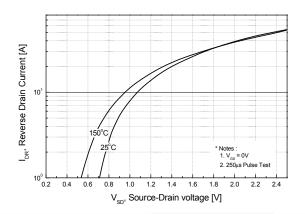


Figure 5. Capacitance Characteristics

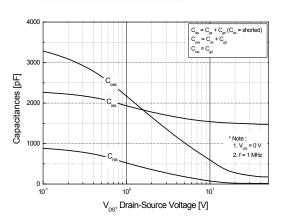
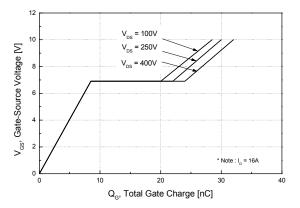


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

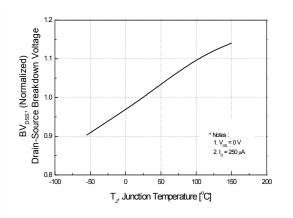


Figure 8. On-Resistance Variation vs. Temperature

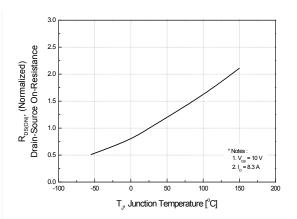
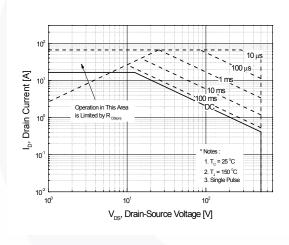


Figure 9. Maximum Safe Operating Area





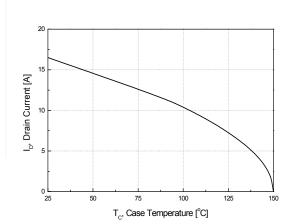


Figure 11. Transient Thermal Response Curve

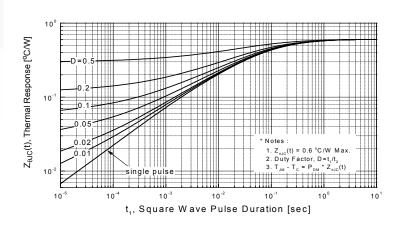


Figure 12. Gate Charge Test Circuit & Waveform

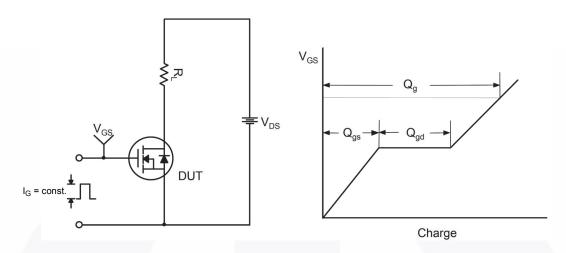


Figure 13. Resistive Switching Test Circuit & Waveforms

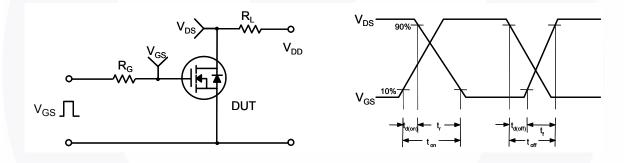
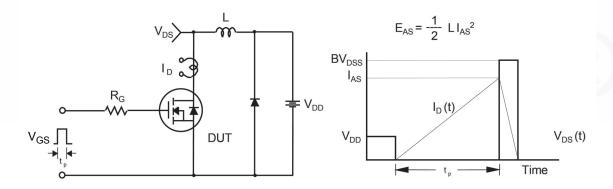


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



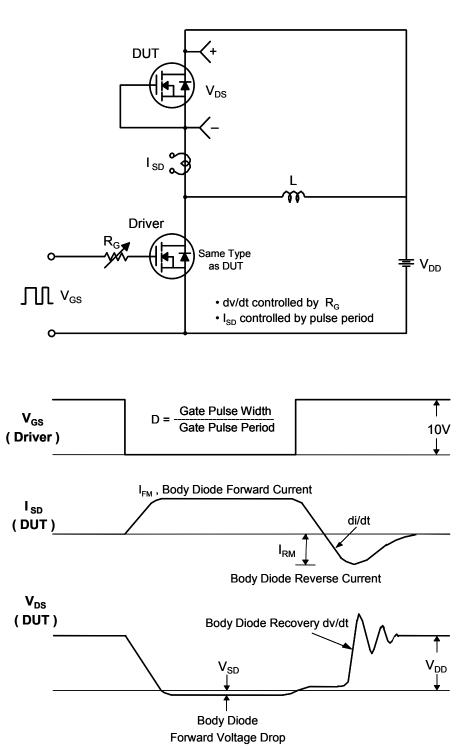
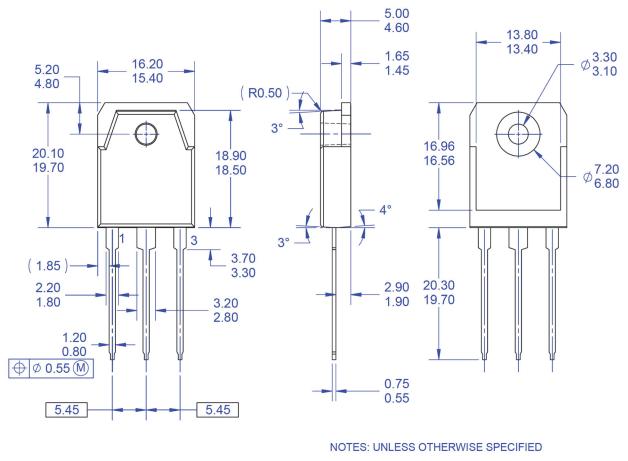
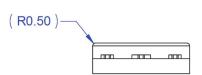


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- **DIMENSION AND TOLERANCING PER** ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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